Power MOSFETS

DATASHEET

LM45015NHM8A

N-Channel

Enhancement Mode MOSFET

Leadpower-semi CO., LTD.

sales@leadpower-semi.com

(03) 6577339　FAX：(03) 6577229

www.leadpower-semi.com

Quality Management Systems

ISO 9001:2015 Certificate

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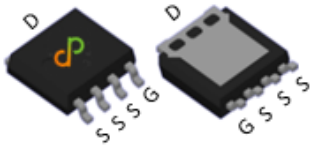
N-Channel Enhancement Mode MOSFET

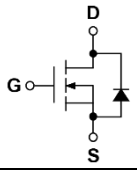
Pin Description

LFPAK56

Top view Bottom view



Symbol



Product Summary

Symbol	N-Channel	Unit
V_{DSS}	45	V
$R_{DS(ON)\text{-}Max}$	1.55	mΩ
ID	181	A

Feature

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant & Halogen-Free
- 100% UIS and Rg Tested
- Moisture Sensitivity Level MSL1

Applications

- DC-to-DC converters
- Switch Mode Power Supply
- Brushless DC motor control

Ordering Information

Orderable Part Number	Package Type	Form	Shipping	Marking
LM45015NHM8A	LFPAK56	Tape & Reel	4000 / Tape & Reel	45015 □□□□□□

Note：□□□□□□ = Lot Code

Absolute Maximum Ratings (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter		N-Channel	Unit
V_{DSS}	Drain-Source Voltage		45	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		175	°C
T_{STG}	Storage Temperature Range		-55 to 175	°C
I_S	Diode Continuous Forward Current	T_C=25°C	61	A
I_{SP}①	Diode Pulse Current	T_C=25°C	183	A
I_{DM}	Pulse Drain Current Tested	T_C=25°C	452	A
I_D	Continuous Drain Current	T_C=25°C	181	A
		T_C=100°C	128	
P_D	Maximum Power Dissipation	T_C=25°C	94	W
		T_C=100°C	47	
I_D	Continuous Drain Current	T_A=25°C	34	A
		T_A=70°C	29	
P_D	Maximum Power Dissipation	T_A=25°C	3.3	W
		T_A=70°C	2.3	
I_{AS}②	Avalanche Current, Single pulse	L=0.1mH	50	A
		L=0.5mH	28	
E_{AS}②	Avalanche Energy, Single pulse	L=0.1mH	125	mJ
		L=0.5mH	196	

Thermal Characteristics

Symbol	Parameter		Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State	1.6	°C/W
$R_{\theta JA}$③	Thermal Resistance-Junction to Ambient	Steady State	45	°C/W

Note ①：Max. current is limited by max. junction temperature.

Note ②：UIS tested and pulse width are limited by maximum junction temperature 175°C

Note ③：Surface Mounted on 1in^2 FR-4 board with 1oz

N-Channel Electrical Characteristics (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250uA	45	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=36V, V_{GS}=0V	-	-	1	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250uA	2.4	2.9	3.5	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$④	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=50A	-	1.25	1.55	mΩ
gfs	Forward Transconductance	V_{DS}=5V, I_{DS}=10A	-	36	-	S
Dynamic Characteristics ⑤						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V, Freq.=1MHz	-	0.7	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=20V, Freq.=1MHz	-	3504	-	pF
C_{oss}	Output Capacitance		-	1144	-	
C_{rss}	Reverse Transfer Capacitance		-	60	-	
$td_{(ON)}$	Turn-on Delay Time	V_{GS}=10V,V_{DS}=25V, I_D=1A,R_{GEN}=1Ω	-	17	-	nS
t_r	Turn-on Rise Time		-	10	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	34	-	
t_f	Turn-off Fall Time		-	74	-	
Q_g	Total Gate Charge	V_{GS}=6V,V_{DS}=25V, I_D=25A		29		nC
Q_g	Total Gate Charge	V_{GS}=10V,V_{DS}=25V, I_D=25A	-	47	-	nC
Q_{gs}	Gate-Source Charge		-	18	-	
Q_{gd}	Gate-Drain Charge		-	8	-	
Source-Drain Characteristics						
V_{SD}④	Diode Forward Voltage	I_{SD}=25A, V_{GS}=0V	-	0.75	1.1	V
t_{rr}	Reverse Recovery Time	I_F=12.5A, V_R=25V dI$_F$/dt=100A/μs	-	48	-	nS
Q_{rr}	Reverse Recovery Charge		-	70	-	nC

Note ④：Pulse test (pulse width≤300us, duty cycle≤2%).
Note ⑤：Guaranteed by design, not subject to production testing.

N-Channel Typical Characteristics

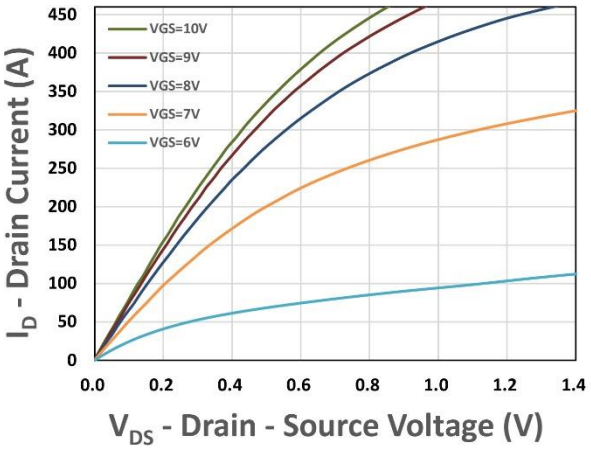


Figure 1. Output Characteristics

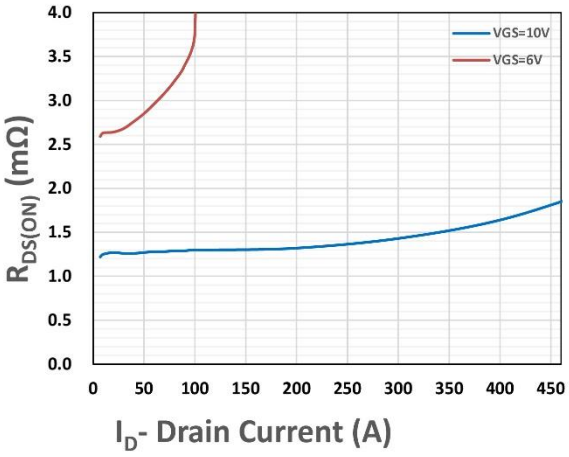


Figure 2. On-Resistance vs. ID

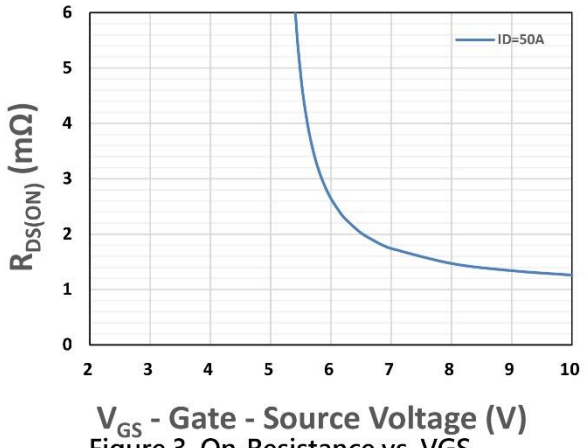


Figure 3. On-Resistance vs. VGS

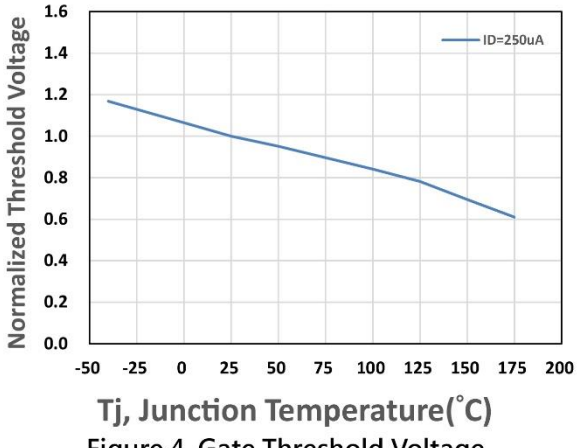


Figure 4. Gate Threshold Voltage

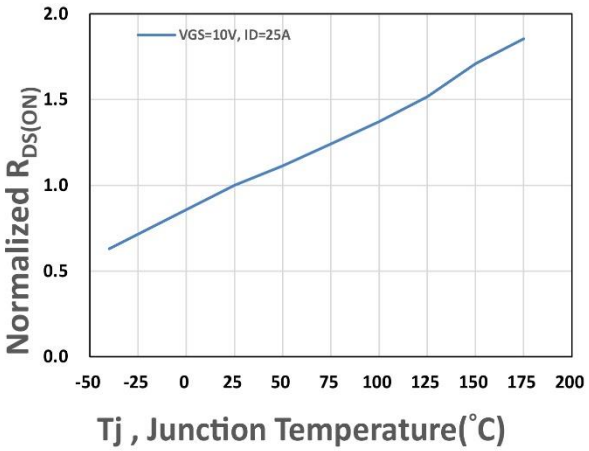


Figure 5. Drain-Source On Resistance

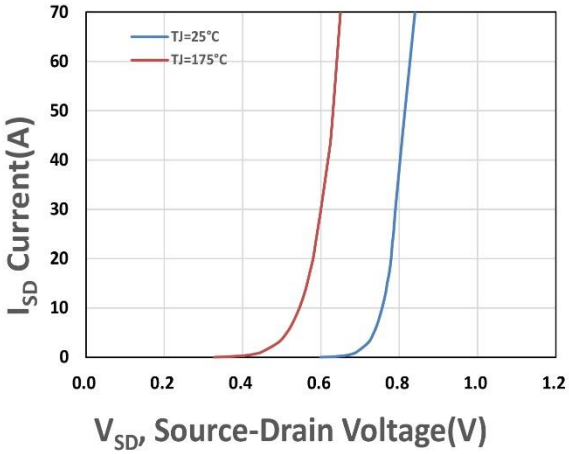
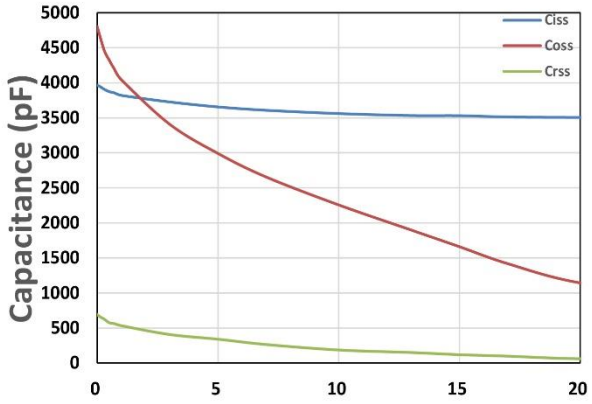
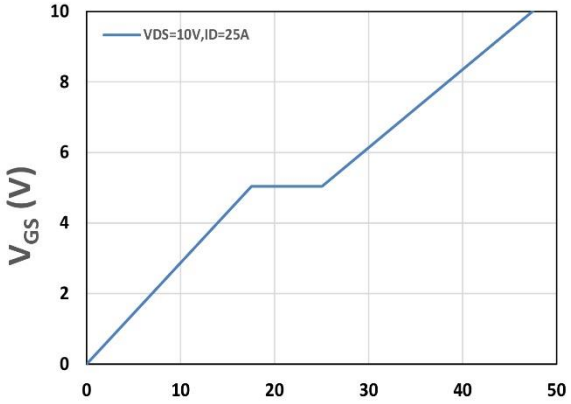


Figure 6. Source-Drain Diode Forward



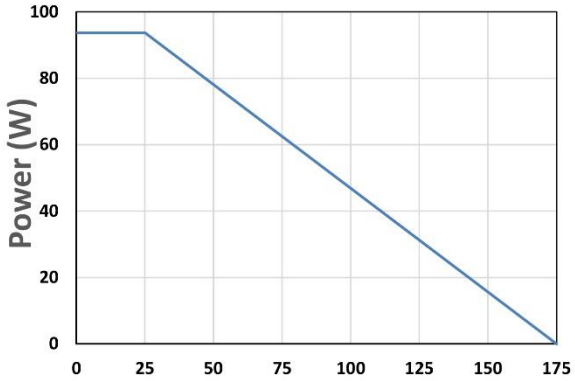
V_{DS} - Drain - Source Voltage (V)

Figure 7. Capacitance



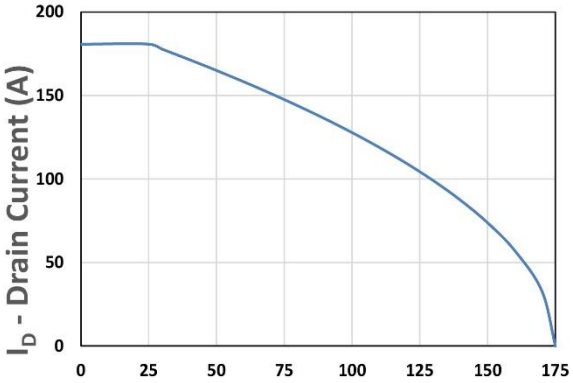
Qg, Total Gate Charge (nC)

Figure 8. Gate Charge Characteristics



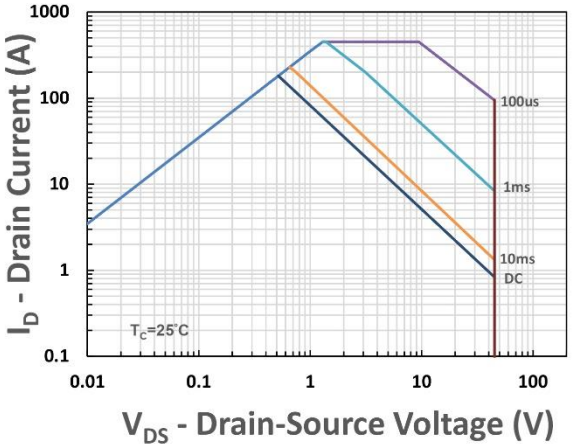
Tc-Case Temperature (˚C)

Figure 9. Power Dissipation



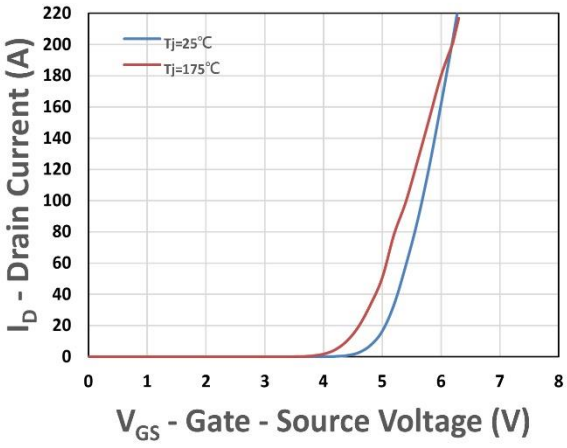
Tc-Case Temperature (˚C)

Figure 10. Drain Current



V_{DS} - Drain-Source Voltage (V)

Figure 11. Safe Operating Area



V_{GS} - Gate - Source Voltage (V)

Figure 12. Transfer Characteristics

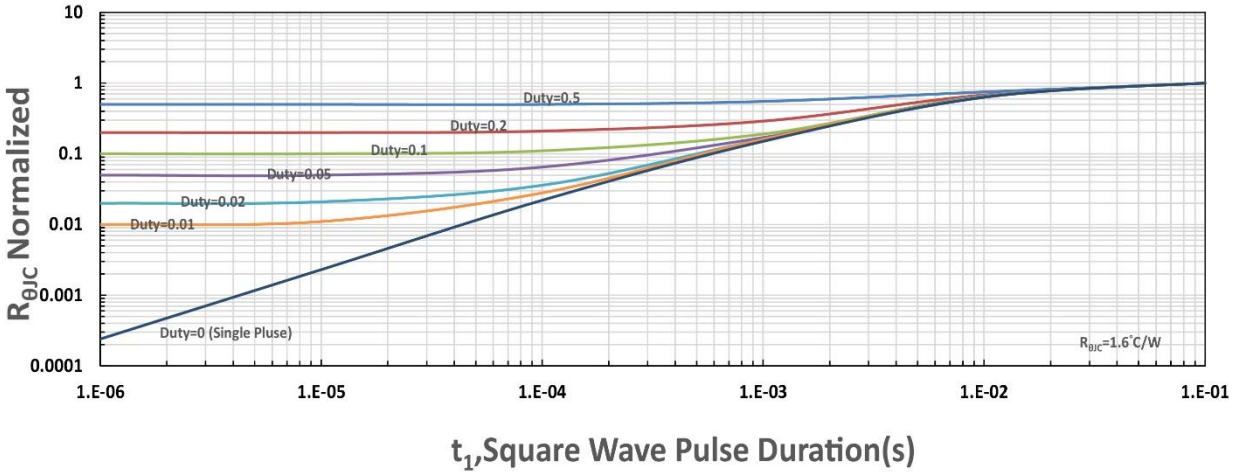


Figure 13. RθJC Transient Thermal Impedance